

Silicon NPN Power Transistors

2N6282 2N6283 2N6284

DESCRIPTION

- With TO-3 package
- Complement to type 2N6285/6286/6287
- High DC current gain
- DARLINGTON

APPLICATIONS

- For use in general-purpose amplifier and low-frequency switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

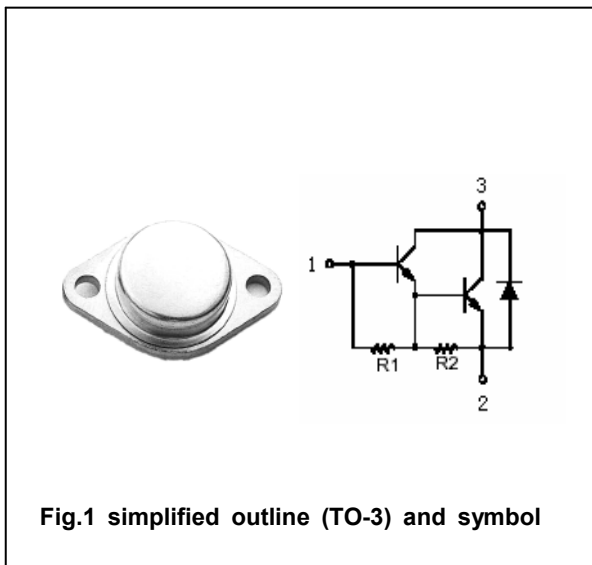


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N6282	60	V
		2N6283	80	
		2N6284	100	
V _{CEO}	Collector-emitter voltage	2N6282	60	V
		2N6283	80	
		2N6284	100	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		20	A
I _{CM}	Collector current-peak		40	A
I _B	Base current		0.5	A
P _D	Total Power Dissipation	T _C =25□	160	W
T _j	Junction temperature		200	□
T _{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.09	□/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N6282	I _C =0.2A ; I _B =0	60			V
		2N6283		80			
		2N6284		100			
V _{CEsat-1}	Collector-emitter saturation voltage		I _C =10A; I _B =40mA			2.0	V
V _{CEsat-2}	Collector-emitter saturation voltage		I _C =20A ; I _B =200mA			3.0	V
V _{BEsat}	Base-emitter saturation voltage		I _C =20A ; I _B =200mA			4.0	V
V _{BE}	Base-emitter on voltage		I _C =10A ; V _{CE} =3V			2.8	V
I _{CEO}	Collector cut-off current	2N6282	V _{CE} =30V; I _B =0			1.0	mA
		2N6283	V _{CE} =40V; I _B =0				
		2N6284	V _{CE} =50V; I _B =0				
I _{CEx}	Collector cut-off current	2N6282	V _{CE} =60V; V _{BE} =-1.5V T _C =150°C			0.5 5.0	mA
		2N6283	V _{CE} =80V; V _{BE} =-1.5V T _C =150°C			0.5 5.0	
		2N6284	V _{CE} =100V; V _{BE} =-1.5V T _C =150°C			0.5 5.0	
I _{EBO}	Emitter cut-off current		V _{EB} =5V; I _C =0			2.0	mA
h _{FE-1}	DC current gain		I _C =10A ; V _{CE} =3V	750		18000	
h _{FE-2}	DC current gain		I _C =20A ; V _{CE} =3V	100			
C _{OB}	Output capacitance		I _E =0; V _{CB} =10V; f=1MHz			400	pF

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PACKAGE OUTLINE

